

4.5 Ω R_{0N}, Triple/Quad SPDT ±5 V, +12 V, +5 V, and +3.3 V Switches

Data Sheet

ADG1633/ADG1634

FEATURES

4.5 Ω typical on resistance
1 Ω on-resistance flatness
Up to 206 mA continuous current
±3.3 V to ±8 V dual-supply operation
3.3 V to 16 V single-supply operation
No V_L supply required
3 V logic-compatible inputs
Rail-to-rail operation
ADG1633

16-lead TSSOP and 16-lead, 3 mm \times 3 mm LFCSP ADG1634

20-lead TSSOP and 20-lead, 4 mm \times 4 mm LFCSP

APPLICATIONS

Communication systems
Medical systems
Audio signal routing
Video signal routing
Automatic test equipment
Data acquisition systems
Battery-powered systems
Sample-and-hold systems
Relay replacements

GENERAL DESCRIPTION

The ADG1633 and ADG1634 are monolithic industrial CMOS (*i*CMOS*) analog switches comprising three independently selectable single-pole, double-throw (SPDT) switches and four independently selectable SPDT switches, respectively.

All channels exhibit break-before-make switching action that prevents momentary shorting when switching channels. An EN input on the ADG1633 (LFCSP and TSSOP packages) and ADG1634 (LFCSP package only) is used to enable or disable the devices. When disabled, all channels are switched off.

The ultralow on resistance and on-resistance flatness of these switches make them ideal solutions for data acquisition and gain switching applications, where low distortion is critical. *i*CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

FUNCTIONAL BLOCK DIAGRAMS

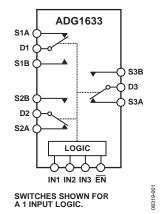


Figure 1. ADG1633 TSSOP and LFCSP

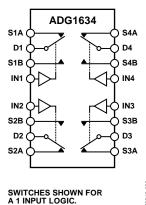


Figure 2. ADG1634 TSSOP

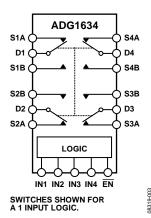


Figure 3. ADG1634 LFCSP

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REVISION HISTORY

8/2016—Rev. A to Rev. B

Changed CP-20-4 to CP-20-10	Throughout
Changes to Figure 5	9
Changes to Figure 7	10
Updated Outline Dimensions	18
Changes to Ordering Guide	19
9/2014—Rev. 0 to Rev. A	
Changes to Figure 26, Figure 27, Figure 28	14

7/2009—Revision 0: Initial Version

SPECIFICATIONS

±5 V DUAL SUPPLY

 V_{DD} = +5 V \pm 10%, V_{SS} = -5 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance (Ron)	4.5			Ωtyp	$V_S = \pm 4.5 \text{ V}, I_S = -10 \text{ mA}$; see Figure 26
	5	7	8	Ω max	$V_{DD} = \pm 4.5 \text{ V}, V_{SS} = \pm 4.5 \text{ V}$
On-Resistance Match Between Channels (ΔR _{ON})	0.12			Ωtyp	$V_S = \pm 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.25	0.3	0.35	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})	1			Ωtyp	$V_S = \pm 4.5 \text{ V, } I_S = -10 \text{ mA}$
	1.3	1.7	2	Ω max	
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.01			nA typ	$V_S = \pm 4.5 \text{ V}, V_D = \pm 4.5 \text{ V}; \text{ see Figure 27}$
3, ,	±0.1	±1.5	±12	nA max	
Drain Off Leakage, I _D (Off)	±0.02			nA typ	$V_S = \pm 4.5 \text{V}, V_D = \pm 4.5 \text{ V}$; see Figure 27
3, 1, 1,	±0.15	±2	±20	nA max	_
Channel On Leakage, ID, IS (On)	±0.02			nA typ	$V_S = V_D = \pm 4.5 \text{ V}$; see Figure 28
3,	±0.15	±2	±20	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	±1			nA typ	$V_{IN} = V_{GND}$ or V_{DD}
			±0.1	μA max	- 100 - 100
Digital Input Capacitance, C _{IN}	8		_0	pF typ	
DYNAMIC CHARACTERISTICS ¹				1 21	
Transition Time, transition	161			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	200	236	264	ns max	V _s = 2.5 V; see Figure 29
t _{on} (EN)	61			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
O. (= · ·)	79	88	98	ns max	$V_s = 2.5 \text{ V}$; see Figure 31
t _{OFF} (EN)	162	00	50	ns typ	$R_L = 300 \Omega$, $C_L = 35 \text{pF}$
COFF (L. V)	199	232	259	ns max	$V_s = 2.5 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t₀	44	232	239	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
break-before-make fille belay, to			30	ns min	$V_{S1} = V_{S2} = 2.5 \text{ V}$; see Figure 30
Charge Injection	-12.5		30	pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF; see Figure 3}.$
Off Isolation	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$;
On isolation	-0-			db typ	see Figure 33
Channel-to-Channel Crosstalk	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 35
Total Harmonic Distortion + Noise (THD + N)	0.3			% typ	$R_L = 110 \Omega$, $V_S = 5 V p-p$, $f = 20 Hz$ to 20 kHz; see Figure 36
–3 dB Bandwidth	103			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34
C _s (Off)	19			pF typ	$V_S = 0 \text{ V, } f = 1 \text{ MHz}$
C _D (Off)	33			pF typ	$V_S = 0 V$, $f = 1 MHz$
C_D , C_S (On)	57			pF typ	$V_S = 0 V$, $f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
I _{DD}	0.001			μA typ	Digital inputs = 0 V or V _{DD}
			1.0	μA max	
V_{DD}/V_{SS}			±3.3/±8	V min/max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, but not subject to production test.

12 V SINGLE SUPPLY

 V_{DD} = 12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0V$ to V_{DD}	V	
On Resistance (R _{ON})	4			Ω typ	$V_s = 0 \text{ V to } 10 \text{ V}, I_s = -10 \text{ mA}; \text{ see Figure 26}$
	4.5	6.5	7.5	Ω max	$V_{DD} = 10.8 \text{ V}, V_{SS} = 0 \text{ V}$
On-Resistance Match Between Channels (ΔR_{ON})	0.12			Ω typ	$V_s = 10 \text{ V}, I_s = -10 \text{ mA}$
	0.25	0.3	0.35	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})	0.9			Ω typ	$V_s = 0 \text{ V to } 10 \text{ V}, I_s = -10 \text{ mA}$
	1.2	1.6	1.9	Ω max	
LEAKAGE CURRENTS					$V_{DD} = 13.2 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.01			nA typ	$V_S = 1 \text{ V}/10 \text{ V}, V_D = 10 \text{ V}/1 \text{ V}; \text{ see Figure 27}$
	±0.1	±1.5	±12	nA max	
Drain Off Leakage, I _D (Off)	±0.02			nA typ	$V_S = 1 \text{ V}/10 \text{ V}, V_D = 10 \text{ V}/1 \text{ V}; \text{ see Figure 27}$
	±0.15	±2	±20	nA max	
Channel On Leakage, ID, IS (On)	±0.02			nA typ	$V_S = V_D = 1 \text{ V or } 10 \text{ V; see Figure } 28$
	±0.15	±2	±20	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, I _{INL} or I _{INH}	±1			nA typ	$V_{IN} = V_{GND}$ or V_{DD}
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	8			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, t _{TRANSITION}	127			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
•	151	182	205	ns max	$V_s = 8 \text{ V}$; see Figure 29
ton (EN)	31			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	38	43	47	ns max	$V_s = 8 \text{ V}$; see Figure 31
t _{off} (EN)	128			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
(a)	152	180	200	ns max	$V_s = 8 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t _D	45	100	200	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
break before make fille belay, to	13		30	ns min	$V_{51} = V_{52} = 8 \text{ V}$; see Figure 30
Charge Injection	-12.4		50	pC typ	$V_S = 6 \text{ V}$, $R_S = 0 \Omega$, $C_L = 1 \text{ nF}$; see Figure 32
Off Isolation	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 33
Channel-to-Channel Crosstalk	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 1 \text{ MHz}$; see Figure 35
Total Harmonic Distortion + Noise (THD + N)	0.3				$R_L = 110 \Omega$, $V_S = 5 V p-p$, $f = 20 Hz$ to $20 kHz$;
				% typ	see Figure 36
–3 dB Bandwidth	109			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34
C _s (Off)	19			pF typ	$V_s = 6 \text{ V}, f = 1 \text{ MHz}$
C_D (Off)	32			pF typ	$V_s = 6 \text{ V}, f = 1 \text{ MHz}$
C_D , C_S (On)	56			pF typ	$V_s = 6 \text{ V}, f = 1 \text{ MHz}$
POWER REQUIREMENTS					$V_{DD} = 12 \text{ V}$
I_{DD}	0.001			μA typ	Digital inputs = 0 V or V _{DD}
			1.0	μA max	
TSSOP	300			μA typ	Digital inputs = 5 V
			480	μA max	
LFCSP	375			μA typ	Digital inputs = 5 V
			600	μA max	
$V_{\mathtt{DD}}$			3.3/16	V min/max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, but not subject to production test.

5 V SINGLE SUPPLY

 V_{DD} = 5 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Tuble 3.		−40°C to	−40°C to		
Parameter		+85°C	+125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0VtoV_{DD}$	V	
On Resistance (R _{ON})				Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA; see Figure 26}$
	10	12.5	14	Ω max	$V_{DD} = 4.5 \text{ V}, V_{SS} = 0 \text{ V}$
On-Resistance Match Between Channels (ΔR_{ON})	0.15			Ω typ	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.3	0.35	0.4	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})	1.7			Ω typ	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA}$
	2.3	2.7	3	Ω max	
LEAKAGE CURRENTS					$V_{DD} = 5.5 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.01			nA typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}; \text{ see Figure 27}$
	±0.1	±1.5	±12	nA max	
Drain Off Leakage, I _D (Off)	±0.02			nA typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}; \text{ see Figure 27}$
	±0.15	±2	±20	nA max	
Channel On Leakage, ID, IS (On)	±0.02			nA typ	$V_S = V_D = 1 \text{ V or } 4.5 \text{ V; see Figure } 28$
	±0.15	±2	±20	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	±1			nA typ	$V_{IN} = V_{GND}$ or V_{DD}
·			±0.1	μA max	
Digital Input Capacitance, C _{IN}	8			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, trransition	199			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	254	303	337	ns max	V _s = 2.5 V; see Figure 29
ton (EN)	68			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	90	102	110	ns max	$V_s = 2.5 \text{ V}$; see Figure 31
t _{OFF} (EN)	201			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	256	300	333	ns max	V _s = 2.5 V; see Figure 31
Break-Before-Make Time Delay, t _D	57			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
Steam Select mane time Selay, is			37	ns min	$V_{S1} = V_{S2} = 2.5 \text{ V}$; see Figure 30
Charge Injection	- 5		.	pC typ	$V_S = 2.5 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}; \text{ see Figure 32}$
Off Isolation	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 33
Channel-to-Channel Crosstalk	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 35
Total Harmonic Distortion + Noise (THD + N)	0.27			% typ	$R_L = 110 \Omega$, $f = 20 Hz$ to $20 kHz$, $V_S = 3.5 V p-p$;
, , , , , , , , , , , , , , , , , , , ,				7. 3/1	see Figure 36
–3 dB Bandwidth	104			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34
C _s (Off)	21			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
C _D (Off)	37			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
C_D , C_S (On)	62			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS					$V_{DD} = 5.5 \text{ V}$
I _{DD}	0.001			μA typ	Digital inputs = 0 V or V _{DD}
			1.0	μA max	
V_{DD}			3.3/16	V min/max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, but not subject to production test.

3.3 V SINGLE SUPPLY

 V_{DD} = 3.3 V, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 4.

Parameter		−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0VtoV_{DD}$	V	
On Resistance (R _{ON})		15	16.5	Ωtyp	$V_S = 0 \text{ V to V}_{DD}$, $I_S = -10 \text{ mA}$; see Figure 26, $V_{DD} = 3.3 \text{ V}$, $V_{SS} = 0 \text{ V}$
On-Resistance Match Between Channels (ΔRoN)	0.25	0.28	0.3	Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
On-Resistance Flatness (R _{FLAT(ON)})	5	5.5	6.5	Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 3.6 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.01			nA typ	$V_S = 0.6 \text{ V/3 V}, V_D = 3 \text{ V/0.6 V}; \text{ see Figure 27}$
	±0.1	±1.5	±12	nA max	
Drain Off Leakage, I _D (Off)	±0.01			nA typ	$V_S = 0.6 \text{ V/3 V}, V_D = 3 \text{ V/0.6 V}; \text{ see Figure 27}$
	±0.15	±2	±20	nA max	
Channel On Leakage, ID, IS (On)	±0.01			nA typ	$V_S = V_D = 0.6 \text{ V or 3 V; see Figure 28}$
	±0.15	±2	±20	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, I _{INL} or I _{INH}	±1			nA typ	$V_{IN} = V_{GND}$ or V_{DD}
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	8			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, trransition	309			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	429	466	508	ns max	V _s = 1.5 V; see Figure 29
$t_{ON}(\overline{EN})$	132			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	184	201	210	ns max	V _s = 1.5 V; see Figure 31
$t_{OFF}(\overline{EN})$	313			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	416	470	509	ns max	$V_s = 1.5 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t _D	81			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
,, <u>, , , , , , , , , , , , , , , , , ,</u>			48	ns min	$V_{S1} = V_{S2} = 1.5 \text{ V}$; see Figure 30
Charge Injection	-10			pC typ	$V_S = 1.5 \text{ V}$, $R_S = 0 \Omega$, $C_L = 1 \text{ nF}$; see Figure 32
Off Isolation	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
				3,1	see Figure 33
Channel-to-Channel Crosstalk	-64			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 35
Total Harmonic Distortion + Noise (THD + N)				% typ	$R_L = 110 \Omega$, $f = 20 Hz$ to $20 kHz$, $V_S = 2 V p-p$; see Figure 36
–3 dB Bandwidth	117			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34
C _s (Off)	22			pF typ	V _S = 1.5 V, f = 1 MHz
C _D (Off)	39			pF typ	$V_S = 1.5 \text{ V, } f = 1 \text{ MHz}$
C _D , C _S (On)	64			pF typ	$V_S = 1.5 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS					V _{DD} = 3.6 V
I _{DD}	0.001			μA typ	Digital inputs = 0 V or V _{DD}
			1.0	μA max	
V_{DD}			3.3/16	V min/max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, but not subject to production test.

CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 5. ADG1633

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, S OR D				
$V_{DD} = +5 \text{ V}, V_{SS} = -5 \text{ V}$				
TSSOP ($\theta_{JA} = 112.6$ °C/W)	126	84	56	mA max
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	206	126	70	mA max
$V_{DD} = 12 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ($\theta_{JA} = 112.6$ °C/W)	133	87	56	mA max
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	213	133	73	mA max
$V_{DD} = 5 V$, $V_{SS} = 0 V$				
TSSOP ($\theta_{JA} = 112.6$ °C/W)	98	70	45	mA max
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	157	105	63	mA max
$V_{DD} = 3.3 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ($\theta_{JA} = 112.6$ °C/W)	77	56	38	mA max
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	129	87	56	mA max

Table 6. ADG1634

Parameter	25°C	85°C	125°C	Unit	
CONTINUOUS CURRENT, S OR D					
$V_{DD} = +5 \text{ V}, V_{SS} = -5 \text{ V}$					
TSSOP ($\theta_{JA} = 95^{\circ}\text{C/W}$)	112	77	52	mA max	
LFCSP ($\theta_{JA} = 30.4$ °C/W)	220	136	73	mA max	
$V_{DD} = 12 \text{ V}, V_{SS} = 0 \text{ V}$					
TSSOP ($\theta_{JA} = 95^{\circ}C/W$)	119	80	52	mA max	
LFCSP ($\theta_{JA} = 30.4$ °C/W)	234	140	73	mA max	
$V_{DD} = 5 \text{ V}, V_{SS} = 0 \text{ V}$					
TSSOP ($\theta_{JA} = 95^{\circ}\text{C/W}$)	87	63	42	mA max	
LFCSP ($\theta_{JA} = 30.4$ °C/W)	171	112	66	mA max	
$V_{DD} = 3.3 \text{ V, } V_{SS} = 0 \text{ V}$					
TSSOP ($\theta_{JA} = 95^{\circ}C/W$)	70	52	35	mA max	
LFCSP ($\theta_{JA} = 30.4$ °C/W)	140	94	59	mA max	

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 7.

Table 7.					
Parameter	Rating				
V _{DD} to V _{SS}	18 V				
V _{DD} to GND	−0.3 V to +18 V				
V _{ss} to GND	+0.3 V to −18 V				
Analog Inputs ¹	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V or}$ 30 mA, whichever occurs first				
Digital Inputs ¹	GND $- 0.3 \text{ V}$ to $\text{V}_{DD} + 0.3 \text{ V}$ or 30 mA, whichever occurs first				
Peak Current, S or D	450 mA (pulsed at 1 ms, 10% duty cycle maximum)				
Continuous Current, S or D ²	Data + 15%				
Operating Temperature Range					
Industrial (Y Version)	−40°C to +125°C				
Storage Temperature Range	−65°C to +150°C				
Junction Temperature	150°C				
16-Lead TSSOP, θ _{JA} Thermal Impedance, 0 Airflow (4- Layer Board)	112.6°C/W				
20-Lead TSSOP, θ _{JA} Thermal Impedance, 0 Airflow (4-Layer Board)	95°C/W				
16-Lead LFCSP (3 mm × 3 mm), θ _{JA} Thermal Impedance, 0 Airflow (4-Layer Board)	48.7°C/W				
16-Lead LFCSP (4 mm × 4 mm), θ _{JA} Thermal Impedance, 0 Airflow (4-Layer Board)	30.4°C/W				
Reflow Soldering Peak Temperature, Pb free	260°C				

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

² See Table 5 and Table 6.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

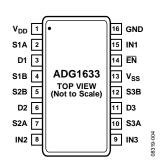


Figure 4. ADG1633 TSSOP Pin Configuration

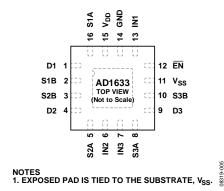


Figure 5. ADG1633 LFCSP Pin Configuration

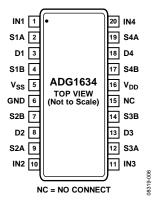
Table 8. ADG1633 Pin Function Descriptions

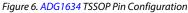
Р	Pin No.		
TSSOP	LFCSP	Mnemonic	Description
1	15	V_{DD}	Most Positive Power Supply Potential.
2	16	S1A	Source Terminal 1A. Can be an input or an output.
3	1	D1	Drain Terminal 1. Can be an input or an output.
4	2	S1B	Source Terminal 1B. Can be an input or an output.
5	3	S2B	Source Terminal 2B. Can be an input or an output.
6	4	D2	Drain Terminal 2. Can be an input or an output.
7	5	S2A	Source Terminal 2A. Can be an input or an output.
8	6	IN2	Logic Control Input 2.
9	7	IN3	Logic Control Input 3.
10	8	S3A	Source Terminal 3A. Can be an input or an output.
11	9	D3	Drain Terminal 3. Can be an input or an output.
12	10	S3B	Source Terminal 3B. Can be an input or an output.
13	11	Vss	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.
14	12	EN	Active Low Digital Input. When this pin is high, the device is disabled and all switches are off. When this pin is low, INx logic inputs determine the on switches.
15	13	IN1	Logic Control Input 1.
16	14	GND	Ground (0 V) Reference.
N/A	17	EP	Exposed Pad. The exposed pad is tied to the substrate, Vss.

Table 9. ADG1633 Truth Table

EN	INx	SxA	SxB
1	X ¹	Off	Off
0	0	Off	On
0	1	On	Off

 $^{^{1}}$ X = don't care.





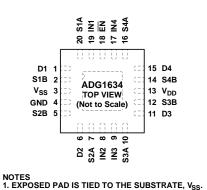


Figure 7. ADG1634 LFCSP Pin Configuration

Table 10. ADG1634 Pin Function Descriptions

Pin No.						
TSSOP	LFCSP	Mnemonic	Description			
1	19	IN1	Logic Control Input 1.			
2	20	S1A	Source Terminal 1A. Can be an input or an output.			
3	1	D1	Drain Terminal 1. Can be an input or an output.			
4	2	S1B	Source Terminal 1B. Can be an input or an output.			
5	3	Vss	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.			
6	4	GND	Ground (0 V) Reference.			
7	5	S2B	Source Terminal 2B. Can be an input or an output.			
8	6	D2	Drain Terminal 2. Can be an input or an output.			
9	7	S2A	Source Terminal 2A. Can be an input or an output.			
10	8	IN2	Logic Control Input 2.			
11	9	IN3	Logic Control Input 3.			
12	10	S3A	Source Terminal 3A. Can be an input or an output.			
13	11	D3	Drain Terminal 3. Can be an input or an output.			
14	12	S3B	Source Terminal 3B. Can be an input or an output.			
15	N/A	NC	No Connect.			
16	13	V_{DD}	Most Positive Power Supply Potential.			
17	14	S4B	Source Terminal 4B. Can be an input or an output.			
18	15	D4	Drain Terminal 4. Can be an input or an output.			
19	16	S4A	Source Terminal 4A. Can be an input or an output.			
20	17	IN4	Logic Control Input 4.			
N/A	18	ĒN	Active Low Digital Input. When this pin is high, the device is disabled and all switches are off. When this pin is low, INx logic inputs determine the on switches.			
N/A	21	EP	Exposed Pad. The exposed pad is tied to the substrate, Vss.			

Table 11. ADG1634 TSSOP Truth Table

INx	SxA	SxB
0	Off	On
1	On	Off

Table 12. ADG1634 LFCSP Truth Table

EN	INx	SxA	SxB
1	X ¹	Off	Off
0	0	Off	On
0	1	On	Off

 $^{^{1}}$ X = don't care.

TYPICAL PERFORMANCE CHARACTERISTICS

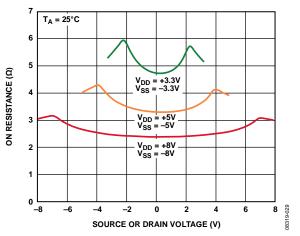


Figure 8. On Resistance vs. V_D (V_S), Dual Supply

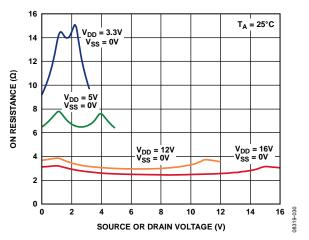


Figure 9. On Resistance vs. VD (Vs), Single Supply

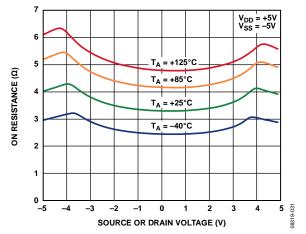


Figure 10. On Resistance vs. V_D (V_S) for Different Temperatures, $\pm 5 V$ Dual Supply

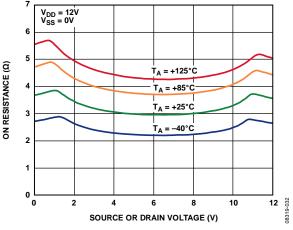


Figure 11. On Resistance vs. V_D (V_S) for Different Temperatures, 12 V Single Supply

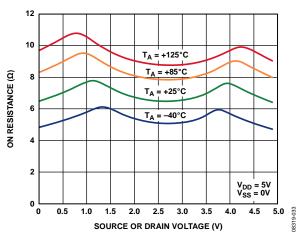


Figure 12. On Resistance vs. V_D (V_S) for Different Temperatures, 5 V Single Supply

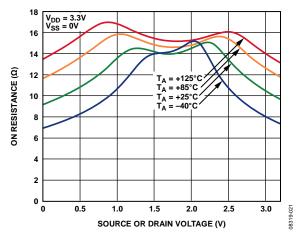


Figure 13. On Resistance vs. V_D (V_s) for Different Temperatures, 3.3 V Single Supply

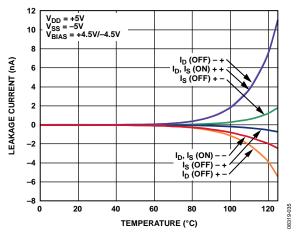


Figure 14. ADG1633 Leakage Currents vs. Temperature, ±5 V Dual Supply

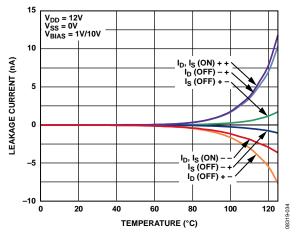


Figure 15. ADG1633 Leakage Currents vs. Temperature, 12 V Single Supply

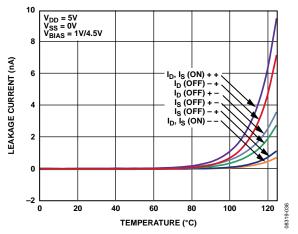


Figure 16. ADG1633 Leakage Currents vs. Temperature, 5 V Single Supply

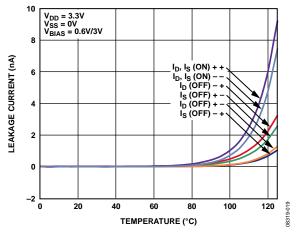


Figure 17. ADG1633 Leakage Currents vs. Temperature, 3.3 V Single Supply

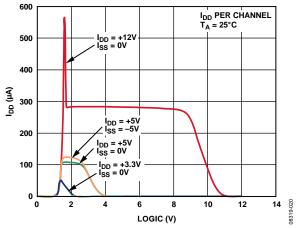


Figure 18. I_{DD} vs. Logic Level

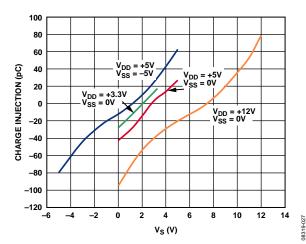


Figure 19. Charge Injection vs. Source Voltage

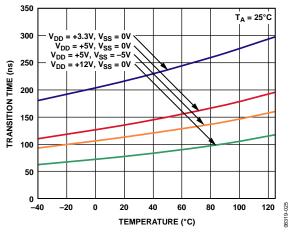


Figure 20. Transition Time vs. Temperature

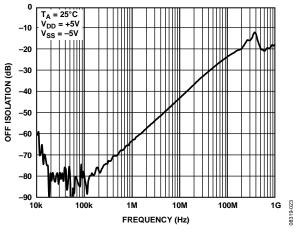


Figure 21. Off Isolation vs. Frequency

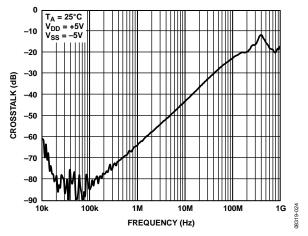


Figure 22. Crosstalk vs. Frequency

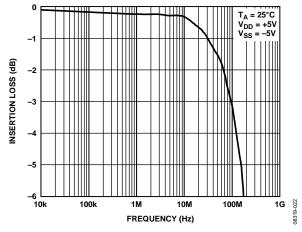


Figure 23. On Response vs. Frequency

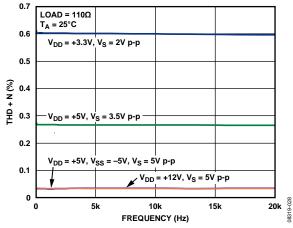


Figure 24. THD + N vs. Frequency

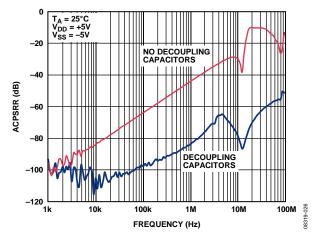


Figure 25. ACPSRR vs. Frequency

TEST CIRCUITS

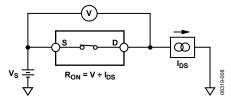


Figure 26. On Resistance

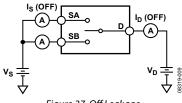


Figure 27. Off Leakage

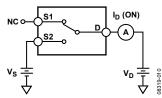


Figure 28. On Leakage

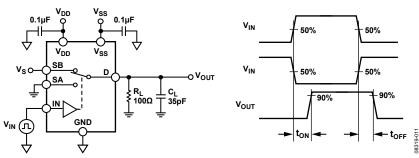


Figure 29. Switching Timing

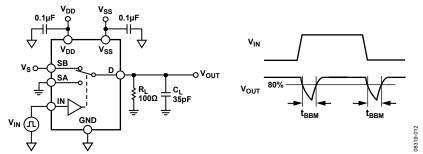


Figure 30. Break-Before-Make Delay, t_D

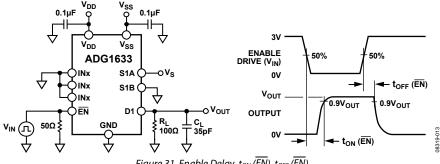


Figure 31. Enable Delay, $t_{ON}(\overline{EN})$, $t_{OFF}(\overline{EN})$

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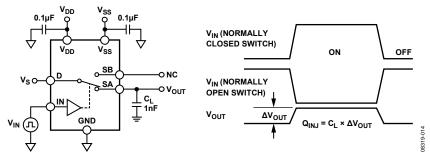


Figure 32. Charge Injection

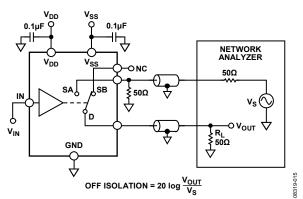


Figure 33. Off Isolation

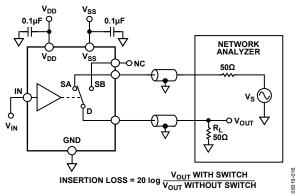


Figure 34. Bandwidth

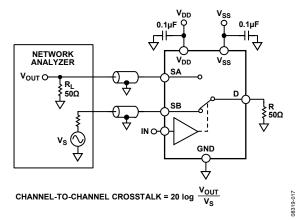


Figure 35. Channel-to-Channel Crosstalk

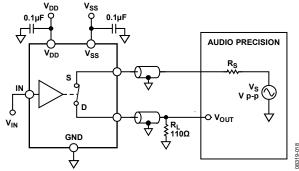


Figure 36. THD + Noise

TERMINOLOGY

Ron

Ohmic resistance between Terminal D and Terminal S.

 ΔR_{ON}

The difference between the R_{ON} of any two channels.

R_{FLAT(ON}

The difference between the maximum and minimum value of on resistance measured.

Is (Off)

Source leakage current when the switch is off.

 I_D (Off)

Drain leakage current when the switch is off.

 I_D , I_S (On)

Channel leakage current when the switch is on.

 $V_D(V_S)$

Analog voltage on Terminal D and Terminal S.

Cs (Off)

Channel input capacitance for off condition.

C_D (Off)

Channel output capacitance for off condition.

 C_D , C_S (On)

On switch capacitance.

CIN

Digital input capacitance.

 $t_{ON}(\overline{EN})$

Delay time between the 50% and 90% points of the digital input and switch on condition.

 $t_{OFF}(\overline{EN})$

Delay time between the 50% and 90% points of the digital input and switch off condition.

tTRANS

Delay time between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

tввм

Off time measured between the 80% point of both switches when switching from one address state to another.

 V_{I}

Maximum input voltage for Logic 0.

 \mathbf{V}_{IH}

Minimum input voltage for Logic 1.

In. (In)

Input current of the digital input.

Inn

Positive supply current.

 I_{ss}

Negative supply current.

Off Isolation

A measure of unwanted signal coupling through an off channel.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

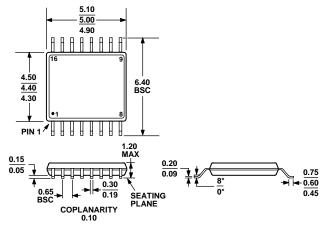
Total Harmonic Distortion + Noise (THD + N)

The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

AC Power Supply Rejection Ratio (ACPSRR)

A measure of the ability of a part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p. The ratio of the amplitude of signal on the output to the amplitude of the modulation is the ACPSRR.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 37. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16) Dimensions shown in millimeters

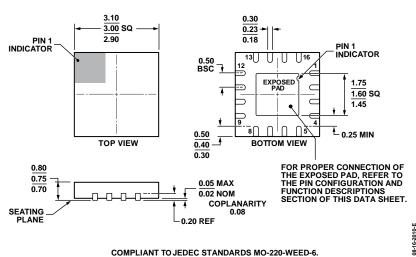
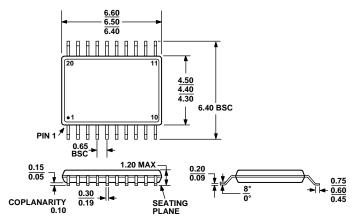


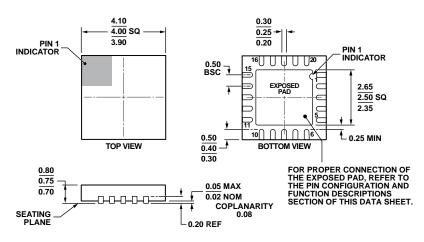
Figure 38. 16-Lead Lead Frame Chip Scale Package [LFCSP]

3 mm × 3 mm and 0.75 mm Package Height (CP-16-22) Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-153-AC

Figure 39. 20-Lead Thin Shrink Small Outline Package [TSSOP] (RU-20) Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-220-WGGD.

Figure 40. 20-Lead Lead Frame Chip Scale Package [LFCSP] 4 mm × 4 mm Body and 0.75 mm Package Height (CP-20-10) Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Description	EN Pin	Package Option	Branding
ADG1633BRUZ	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	Yes	RU-16	
ADG1633BRUZ-REEL7	−40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	Yes	RU-16	
ADG1633BCPZ-REEL7	−40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	Yes	CP-16-22	SD3
ADG1634BRUZ	-40°C to +125°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	No	RU-20	
ADG1634BRUZ-REEL7	−40°C to +125°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	No	RU-20	
ADG1634BCPZ-REEL7	−40°C to +125°C	20-Lead Lead Frame Chip Scale Package [LFCSP]	Yes	CP-20-10	

¹ Z = RoHS Compliant Part.